

P-CHANNEL MOS FIELD EFFECT TRANSISTOR
FOR SWITCHING

DESCRIPTION

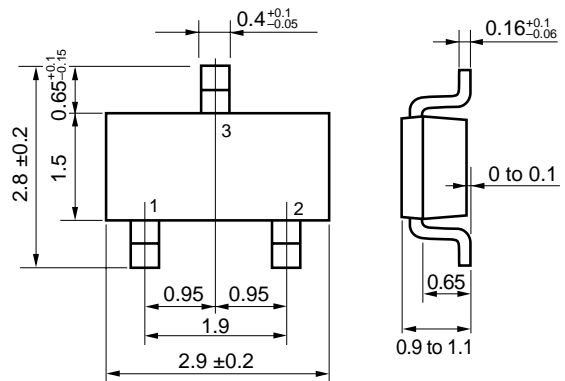
The 2SJ621 is a switching device which can be driven directly by a 1.8 V power source.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 1.8 V drive available
- Low on-state resistance
 $R_{DS(on)1} = 44 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.5 \text{ V, } I_D = -2.0 \text{ A)}$
 $R_{DS(on)2} = 56 \text{ m}\Omega \text{ MAX. (} V_{GS} = -3.0 \text{ V, } I_D = -2.0 \text{ A)}$
 $R_{DS(on)3} = 62 \text{ m}\Omega \text{ MAX. (} V_{GS} = -2.5 \text{ V, } I_D = -2.0 \text{ A)}$
 $R_{DS(on)4} = 105 \text{ m}\Omega \text{ MAX. (} V_{GS} = -1.8 \text{ V, } I_D = -1.5 \text{ A)}$

PACKAGE DRAWING (Unit: mm)



1 : Gate
2 : Source
3 : Drain

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SJ621	SC-96 (Mini Mold Thin Type)

Marking: XG

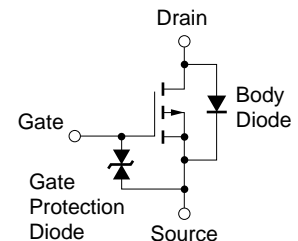
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	-12	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	∓ 8.0	V
Drain Current (DC) ($T_A = 25^\circ\text{C}$)	$I_{D(DC)}$	∓ 3.5	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	∓ 12	A
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T1}	0.2	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$) ^{Note2}	P_{T2}	1.25	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

- Notes 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$
2. Mounted on FR-4 board, $t \leq 5 \text{ sec}$.

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

EQUIVALENT CIRCUIT

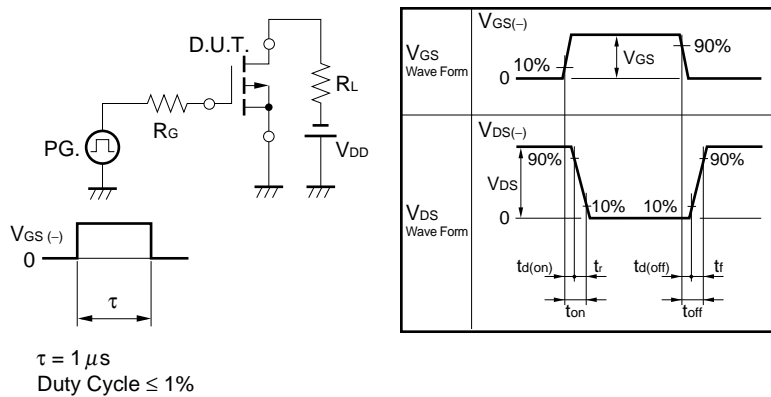


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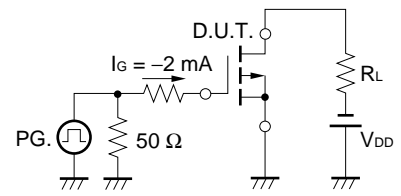
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -12 V, V _{GS} = 0 V			-10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±8.0 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1.0 mA	0.45		1.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10 V, I _D = -3.5 A	4.0			S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = -4.5 V, I _D = -2.0 A		35	44	mΩ
	R _{DS(on)2}	V _{GS} = -3.0 V, I _D = -2.0 A		42	56	mΩ
	R _{DS(on)3}	V _{GS} = -2.5 V, I _D = -2.0 A		46	62	mΩ
	R _{DS(on)4}	V _{GS} = -1.8 V, I _D = -1.5 A		63	105	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V		630		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		170		pF
Reverse Transfer Capacitance	C _{rss}	f = 1.0 MHz		100		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -6.0 V, I _D = -2.0 A		20		ns
Rise Time	t _r	V _{GS} = -4.0 V		70		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		320		ns
Fall Time	t _f			200		ns
Total Gate Charge	Q _G	V _{DD} = -10 V		6.2		nC
Gate to Source Charge	Q _{GS}	V _{GS} = -4.0 V		1.0		nC
Gate to Drain Charge	Q _{GD}	I _D = -3.5 A		2.0		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 3.5 A, V _{GS} = 0 V		0.84		V

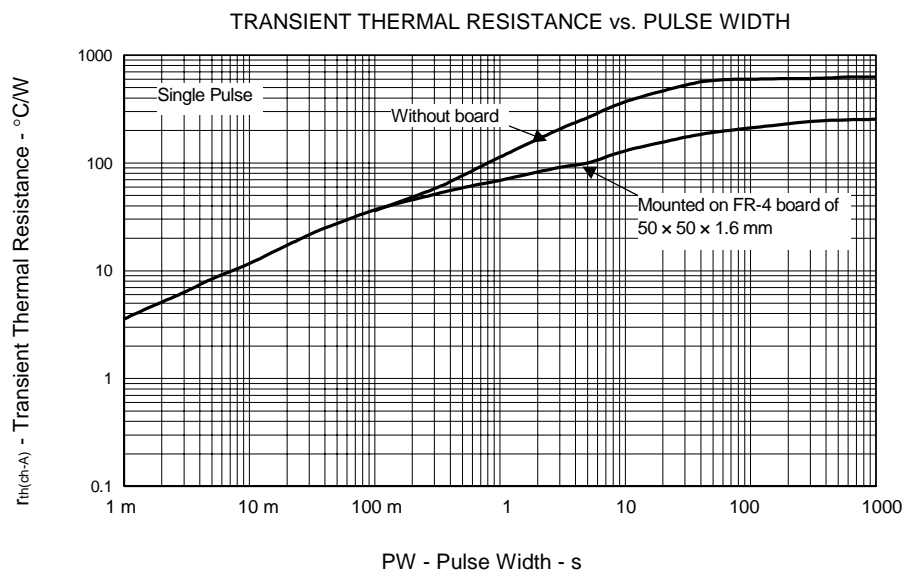
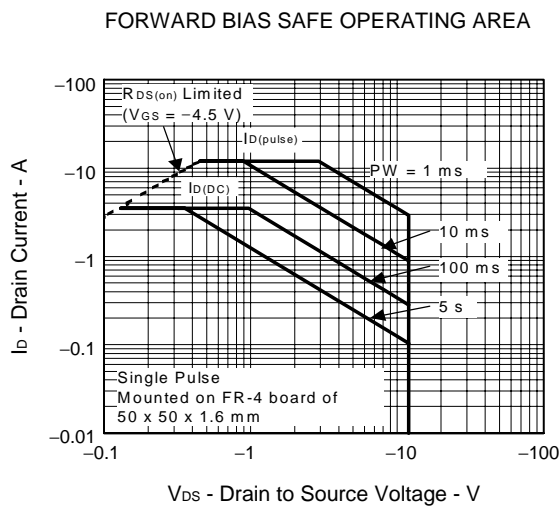
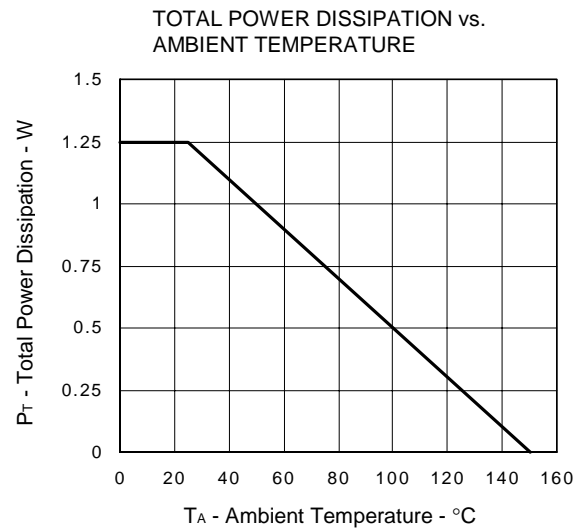
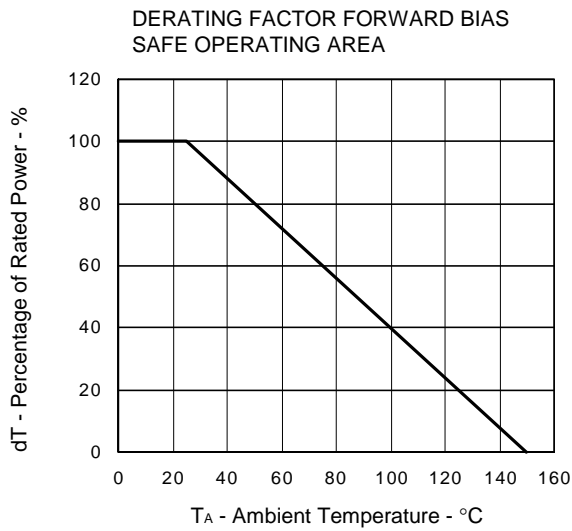
TEST CIRCUIT 1 SWITCHING TIME

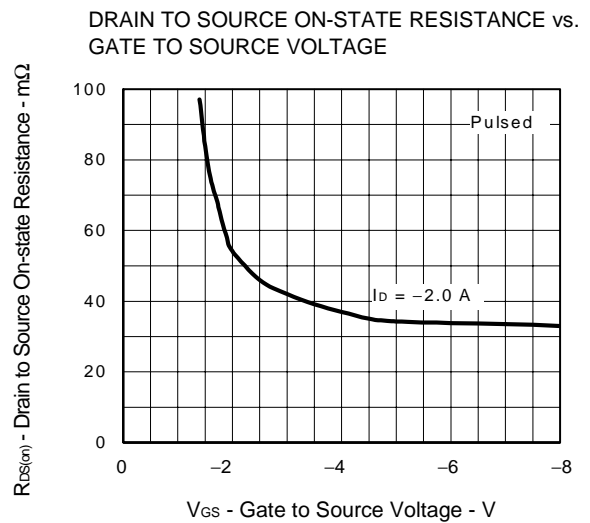
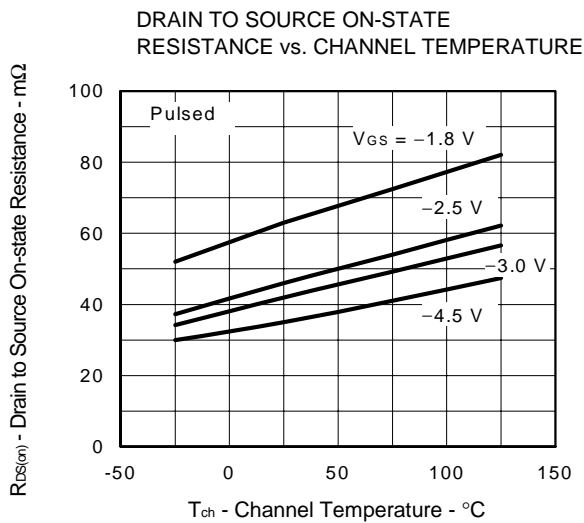
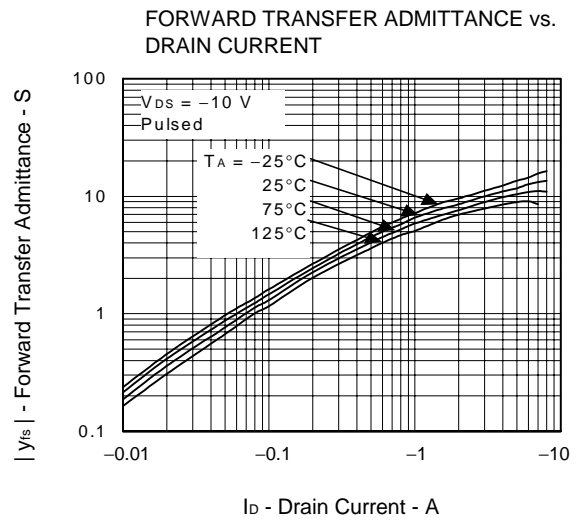
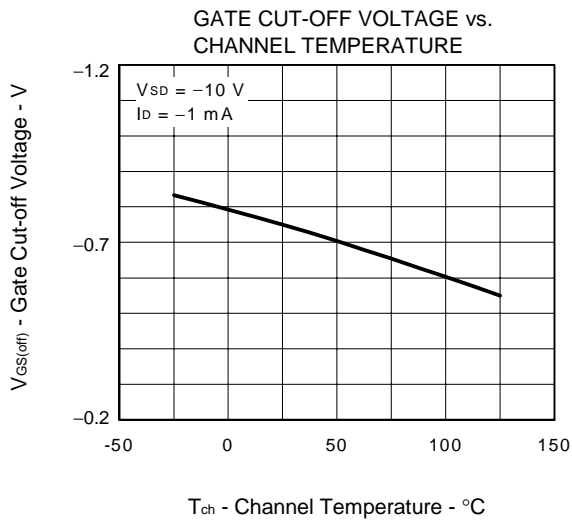
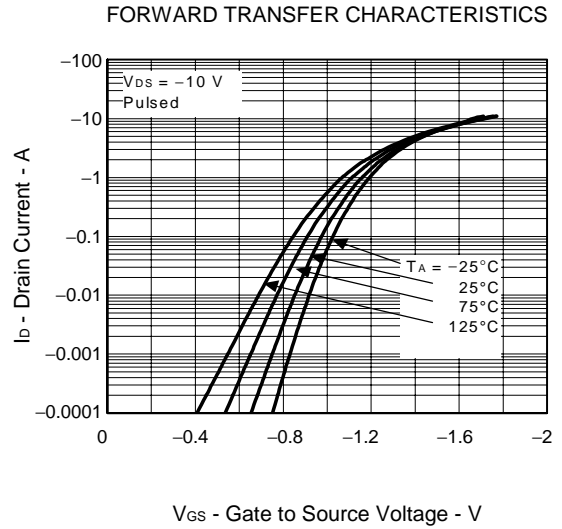
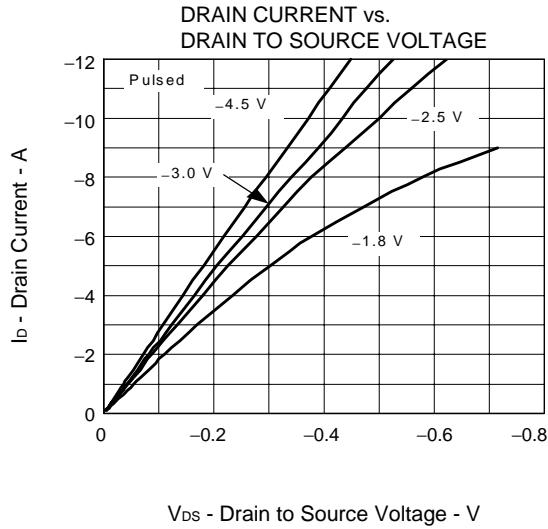


TEST CIRCUIT 2 GATE CHARGE

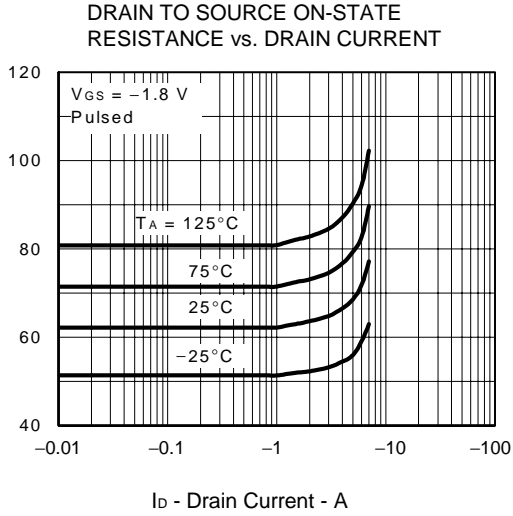


TYPICAL CHARACTERISTICS (T_A = 25°C)

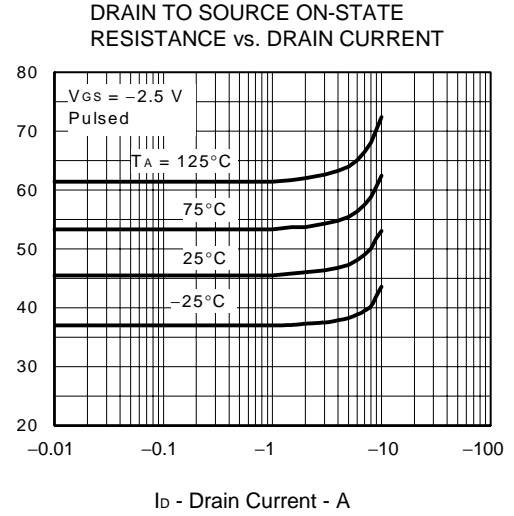




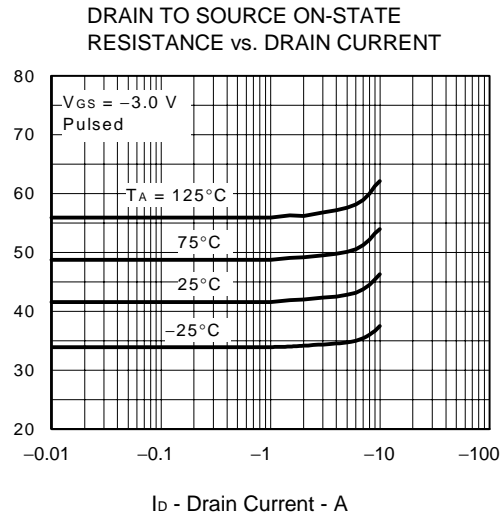
$R_{DS(on)}$ - Drain to Source On-state Resistance - m Ω



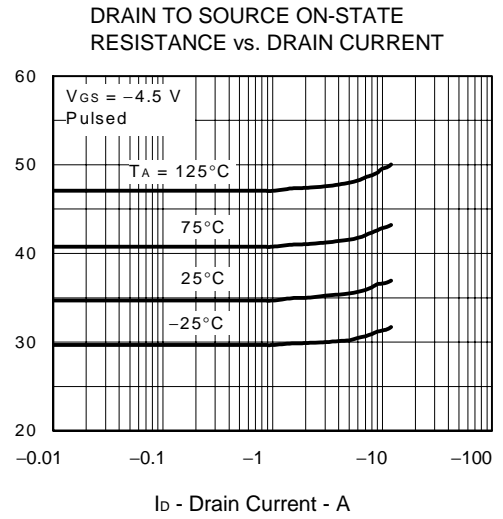
$R_{DS(on)}$ - Drain to Source On-state Resistance - m Ω



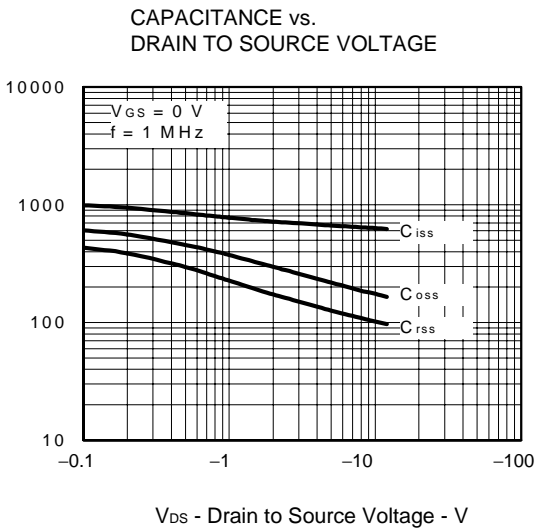
$R_{DS(on)}$ - Drain to Source On-state Resistance - m Ω



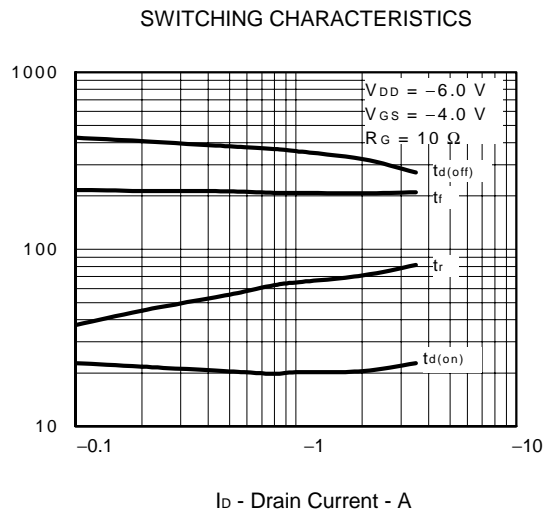
$R_{DS(on)}$ - Drain to Source On-state Resistance - m Ω



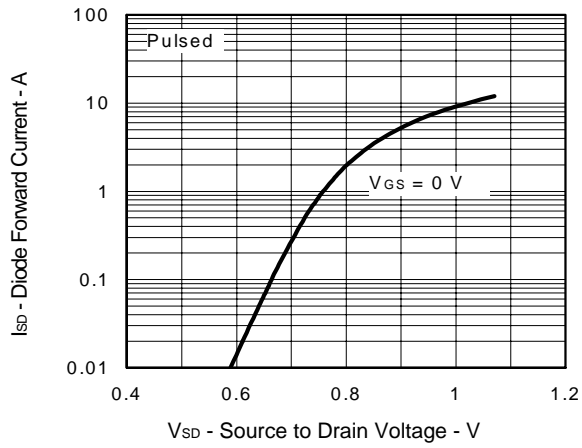
C_{iss} , C_{oss} , C_{rss} - Capacitance - pF



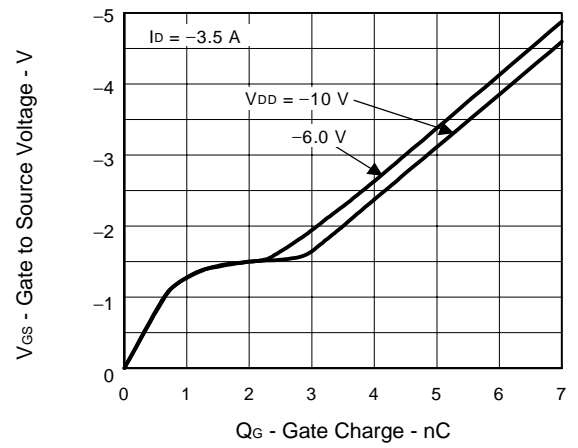
$t_{d(on)}$, t_r , $t_{d(off)}$, t_f - Switching Time - ns



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



[MEMO]

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